

0.7-Ω DUAL SPDT ANALOG SWITCH WITH NEGATIVE RAIL CAPABILITY AND 1.8-V COMPATIBLE INPUT LOGIC

FEATURES

- **Negative Signaling Capability:** Maximum Swing From -2.75 V to 2.75 V ($V_+ = 2.75\text{ V}$)
- **Low ON-State Resistance** ($0.7\text{ }\Omega$ Typ)
- **Excellent ON-State Resistance Matching**
- **1.8-V Compatible Control Input Threshold Independent of V_+**
- **Control Inputs Are 5.5-V Tolerant**
- **2.25-V to 5.5-V Power Supply (V_+)**
- **Low Charge Injection**
- **Specified Break-Before-Make Switching**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**

- **ESD Performance Tested Per JESD 22**
 - 2500-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 200-V Machine Model (A115-A)

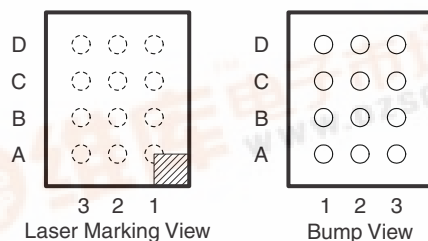
APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio Routing
- Portable Media Players

YFC PACKAGE TERMINAL ASSIGNMENTS

D	NC1	V_+	NC2
C	COM1	GND	COM2
B	NO1	GND	NO2
A	IN1	N.C. ⁽¹⁾	IN2
	1	2	3

YFC PACKAGE



(1) N.C. –No internal connection

DESCRIPTION/ORDERING INFORMATION

The TS5A22366 is a dual single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device features negative signal capability that allows signals below ground to pass through the switch without distortion.

The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications.

The TS5A22366 is available in a ultra small 1.6 mm × 1.2 mm wafer-chip-scale package (WCSP) (0.4 mm pitch) and in a 2 mm × 1.5 mm quad flat (QFN) package (0.5 mm pitch).

ORDERING INFORMATION

T_A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
-40°C to 85°C	NanoFree™ – WCSP (DSBGA) YFC (Pb-free)	Tape and reel	TS5A22366YFCR	3A_

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) YFC: The actual top-side marking has one additional character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



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SUMMARY OF CHARACTERISTICS $V_+ = 3.3 \text{ V}$, $T_A = 25^\circ\text{C}$

Configuration	2:1 Multiplexer/Demultiplexer (2 × SPDT)
Number of channels	2
ON-state resistance (r_{on})	0.8 Ω
ON-state resistance match (Δr_{on})	0.08 Ω
ON-state resistance flatness ($r_{\text{ON(flat)}}$)	0.3 Ω
Turn-on/turn-off time ($t_{\text{ON}}/t_{\text{OFF}}$)	199 ns/182 ns
Break-before-make time (t_{BBM})	7.1 ns
Charge injection (Q_C)	120 pC
Bandwidth (BW)	32 MHz
OFF isolation (O_{ISO})	−70 dB at 100 kHz
Crosstalk (X_{TALK})	−70 dB at 100 kHz
Total harmonic distortion (THD)	0.01%
Package option	12-pin WCSP (YFC)

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

APPLICATION BLOCK DIAGRAM

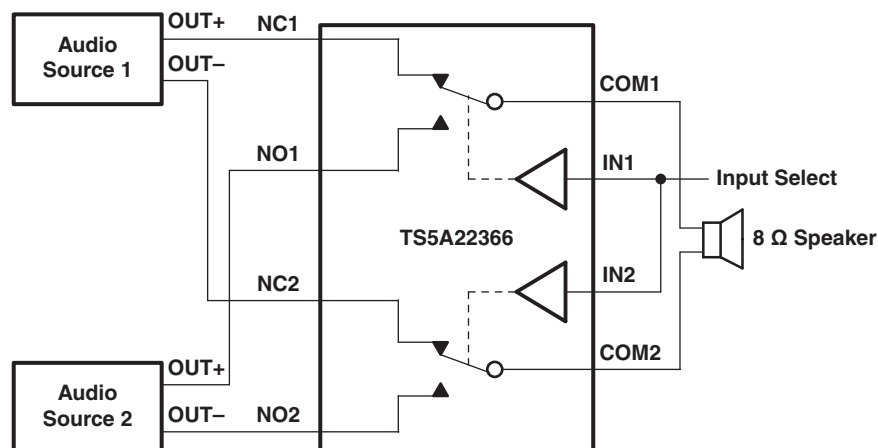


Figure 1. TS5A22366 Application Block Diagram

Negative Signaling Capacity

The TS5A22366 dual SPDT switch features negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input/output signal swing of the device is dependant of the supply voltage V_+ ; the devices pass signals as high as V_+ and as low as $V_+ - 5.5$ V, including signals below ground with minimal distortion.

Table 1 shows the input/output signal swing the user can get with different supply voltages.

Table 1. Input/Output Signal Swing

SUPPLY VOLTAGE, V_+	MINIMUM (V_{NC}, V_{NO}, V_{COM}) = $V_+ - 5.5$	MAXIMUM (V_{NC}, V_{NO}, V_{COM}) = V_+
5.5 V	0 V	5.5 V
4.2 V	-1.3 V	4.2 V
3.3 V	-2.2 V	3.3 V
3 V	-2.5 V	3 V
2.5 V	-3 V	2.5 V

ABSOLUTE MINIMUM AND MAXIMUM RATINGS⁽¹⁾⁽²⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range ⁽³⁾		-0.5	6	V
V _{NC} V _{NO} V _{COM}	Analog voltage range ⁽³⁾⁽⁴⁾⁽⁵⁾		V ₊ - 6	V ₊ + 0.5	V
I _K	Analog port diode current ⁽⁶⁾	V ₊ < V _{NC} , V _{NO} , V _{COM} < 0	-50	50	V
I _{NC} I _{NO} I _{COM}	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V ₊	-150	150	mA
	ON-state peak switch current ⁽⁷⁾		-300	300	
V _I	Digital input voltage range		-0.5	6.5	V
I _{IK}	Digital input clamp current ⁽³⁾⁽⁴⁾	V _{IO} < V _I < 0	-50		mA
I _{GND} I ₊	Continuous current through V ₊ or GND		-100	100	mA
T _{stg}	Storage temperature range		-65	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Requires clamp diodes on analog port to V_+ .
- (7) Pulse at 1-ms duration <10% duty cycle

THERMAL IMPEDANCE RATINGS

				UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	YFC package	106.2	°C/W

- (1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾
 $V_+ = 2.25\text{ V to }2.7\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO} , V _{NC}					V ₊ − 5.5		V ₊	Ω
ON-state resistance	r _{on}	V _{NC} or V _{NO} = V ₊ , 1.5 V, V ₊ − 5.5 V I _{COM} = −100 mA,	Switch ON, See Figure 15	25°C	2.25 V	1		1.8	Ω
				Full				2	
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.5 V, I _{COM} = −100 mA,	Switch ON, See Figure 15	25°C	2.25 V	0.05		1	Ω
				Full				1	
ON-state resistance flatness	r _{on(flat)}	V _{NC} or V _{NO} = V ₊ , 1.5 V, V ₊ − 5.5 V I _{COM} = −100 mA,	Switch ON, See Figure 16	25°C	2.25 V	0.53		1.5	Ω
				Full				1.6	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} = 2.25, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 2.25, V _{NO} = Open, or V _{NO} = 2.25, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 2.25, V _{NC} = Open,	Switch OFF, See Figure 16	25°C	2.7 V	−50		50	nA
				Full		−375		375	
COM ON leakage current	I _{COM(ON)}	V _{NC} and V _{NO} = Open, V _{COM} = V ₊ , V ₊ − 5.5 V,	See Figure 17	25°C	2.7 V	−50		50	nA
				Full		−375		375	
Digital Control Inputs (IN, EN) ⁽²⁾									
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V _{IL}			Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or GND		25°C	2.7 V	−700		700	nA
				Full		−700		700	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY (continued)
 $V_+ = 2.25\text{ V to }2.7\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	2.5 V	193		297	ns
				Full	2.25 V to 2.7 V	350			
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	2.5 V			266	ns
				Full	2.25 V to 2.7 V	320			
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2 R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	2.5 V	1	15.6		ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	2.5 V	91			pC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	2.5 V	51			pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	2.5 V	181			pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	2.5 V	181			pF
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	2.5 V	3			pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	2.5 V	32			MHz
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz,	25°C	2.5 V	–70			dB
			f = 1 MHz,			–50			
			f = 5 MHz,			–35			
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz,	25°C	2.5 V	–70			dB
			f = 1 MHz,			–50			
			f = 5 MHz,			–35			
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	2.5 V	0.02			%
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND,		Full	2.7 V	6		12	μA

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾
 $V_+ = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V _{COM} , V _{NO} , V _{NC}				V ₊ − 0.5		V ₊	Ω
ON-state resistance	r _{on}	V _{NC} or V _{NO} ≤ V ₊ , 1.5 V, V ₊ − 5.5 V, I _{COM} = −100 mA, Switch ON, See Figure 15	25°C	3 V		0.8	1.3	Ω
			Full				1.53	
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.5 V, I _{COM} = −100 mA, Switch ON, See Figure 15	25°C	3 V		0.08	0.17	Ω
			Full				0.3	
ON-state resistance flatness	r _{on(flat)}	V _{NC} or V _{NO} ≤ V ₊ , 1.5 V, V ₊ − 5.5 V, I _{COM} = −100 mA, Switch ON, See Figure 16	25°C	3 V		0.3	0.65	Ω
			Full				0.75	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} = 3, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 3, V _{NO} = Open, or V _{NO} = 3, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 3, V _{NC} = Open, Switch OFF, See Figure 16	25°C	3.6 V		−50	50	nA
			Full			−375	375	
COM ON leakage current	I _{COM(ON)}	V _{NC} and V _{NO} = Open, V _{COM} = V ₊ , V ₊ − 5.5 V, Switch ON, See Figure 17	25°C	3.6 V		−50	50	nA
			Full			−375	375	
Digital Control Inputs (IN, EN) ⁽²⁾								
Input logic high	V _{IH}		Full			1.05	5.5	V
Input logic low	V _{IL}		Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or GND	25°C	3.6 V		−920	920	nA
			Full			−920	920	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (continued)
 $V_+ = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	3.3 V	199		313	ns
				Full	3 V to 3.6 V	370			
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	3.3 V	182		289.9	ns
				Full	3 V to 3.6 V	350			
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2 R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	3.3 V	1	7.1		ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	3.3 V	120			pC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch OFF,	See Figure 18	25°C	3.3 V	50			pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 18	25°C	3.3 V	180			pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	3.3 V	180			pF
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	3.3 V	3			pF
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	3.3 V	32			MHz
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz,	25°C	3.3 V	–70			dB
			f = 1 MHz,			–50			
			f = 5 MHz,			–35			
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz,	25°C	3.3 V	–70			dB
			f = 1 MHz,			–50			
			f = 5 MHz,			–35			
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	3.3 V	0.01			%
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	3.6 V	6		13	μA

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾
 $V_+ = 4.5\text{ V to }5.5\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V _{COM} , V _{NO} , V _{NC}					V ₊ − 5.5		V ₊	Ω
ON-state resistance	r _{on}	V _{NC} or V _{NO} = V ₊ , 1.5V, V ₊ -5.5V I _{COM} = −100 mA,	Switch ON, See Figure 15	25°C	4.5 V	0.7		1	Ω
				Full				1.36	
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.5 V, I _{COM} = −100 mA,	Switch ON, See Figure 15	25°C	4.5 V	0.1		0.2	Ω
				Full				0.3	
ON-state resistance flatness	r _{on(flat)}	V _{NC} or V _{NO} = V ₊ , 1.5V, V ₊ -5.5V I _{COM} = −100 mA,	Switch ON, See Figure 16	25°C	4.5 V	0.135		0.37	Ω
				Full				0.51	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} = 4.5, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 4.5, V _{NO} = Open, or V _{NO} = 4.5, V ₊ − 5.5 V V _{COM} = V ₊ − 5.5 V, 4.5, V _{NC} = Open,	Switch OFF, See Figure 16	25°C	5.5 V	−50		50	nA
				Full				−375	
COM ON leakage current	I _{COM(ON)}	V _{NC} and V _{NO} = Open, V _{COM} = V ₊ , V ₊ − 5.5 V,	Switch ON, See Figure 17	25°C	5.5 V	−50		50	nA
				Full				−375	
Digital Control Inputs (IN, EN) ⁽²⁾									
Input logic high	V _{IH}			Full		1.05		5.5	V
Input logic low	V _{IL}			Full				0.65	V
Input leakage current	I _{IH} , I _{IL}	V _{IN} = 1.8 V or 0		25°C	5.5 V	−1.5		1.5	μA
				Full				−1.5	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (continued)
 $V_+ = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	5 V	230	374	ns	
				Full	4.5 V to 5.5 V		470		
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 300 Ω,	C _L = 35 pF, See Figure 19	25°C	5 V	206	325	ns	
				Full	4.5 V to 5.5 V		380		
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2 R _L = 300 Ω,	C _L = 35 pF, See Figure 20	25°C	3.3 V	1	3	ns	
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 24	25°C	5 V	168		pC	
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch OFF,	See Figure 18	25°C	5 V	48		pF	
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or V ₊ – 5.5 V, Switch ON,	See Figure 18	25°C	5 V	176		pF	
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 18	25°C	5 V	176		pF	
Digital input capacitance	C _I	V _I = V ₊ or GND	See Figure 18	25°C	5 V	3		pF	
Bandwidth	BW	R _L = 50 Ω,	Switch ON, See Figure 20	25°C	5 V	32		MHz	
OFF isolation	O _{ISO}	R _L = 50 Ω, Switch OFF, See Figure 22	f = 100 kHz	25°C	5 V	–70		dB	
			f = 1 MHz			–50			
			f = 5 MHz			–35			
Crosstalk	X _{TALK}	R _L = 50 Ω, Switch ON, See Figure 23	f = 100 kHz	25°C	5 V	–70		dB	
			f = 1 MHz			–50			
			f = 5 MHz			–35			
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	5 V	0.01		%	
Supply									
Positive supply current	I ₊	V _I = 1.8 V or GND		Full	5.5 V	7	14	μA	

TYPICAL PERFORMANCE

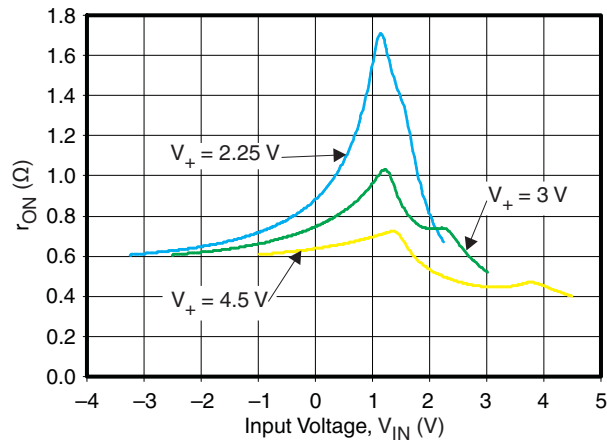


Figure 2. r_{ON} vs V_{IN}

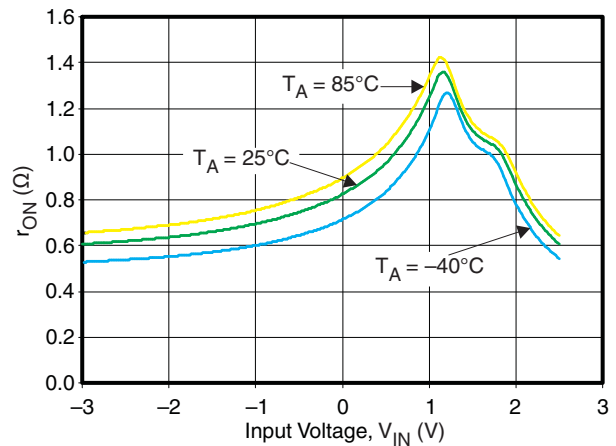


Figure 3. r_{ON} vs V_{IN} ($V_+ = 2.5$ V)

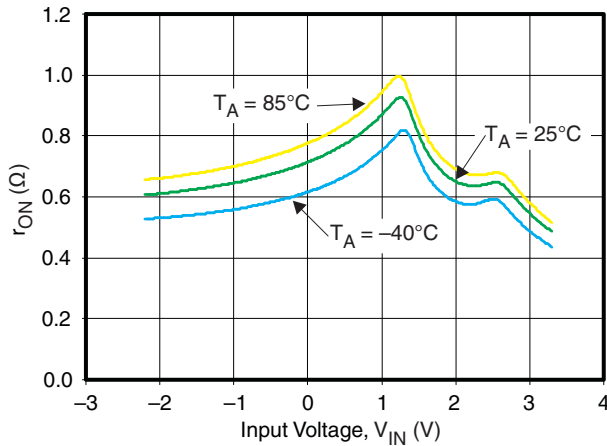


Figure 4. r_{ON} vs V_{IN} ($V_+ = 3.3$ V)

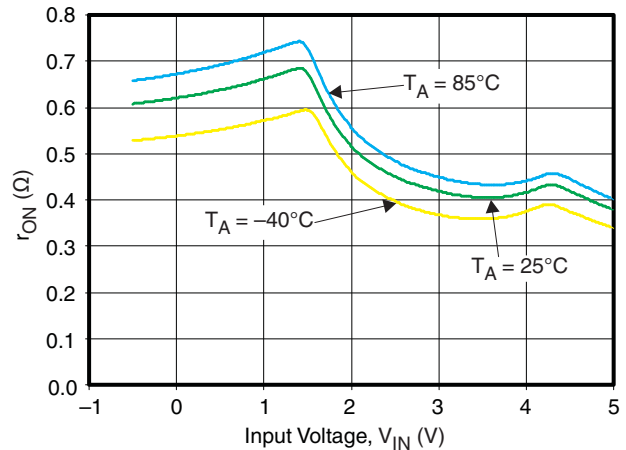


Figure 5. r_{ON} vs V_{IN} ($V_+ = 5$ V)

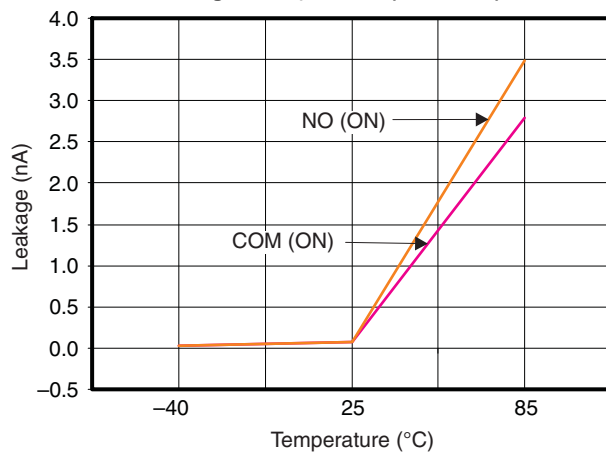


Figure 6. Leakage Current vs Temperature

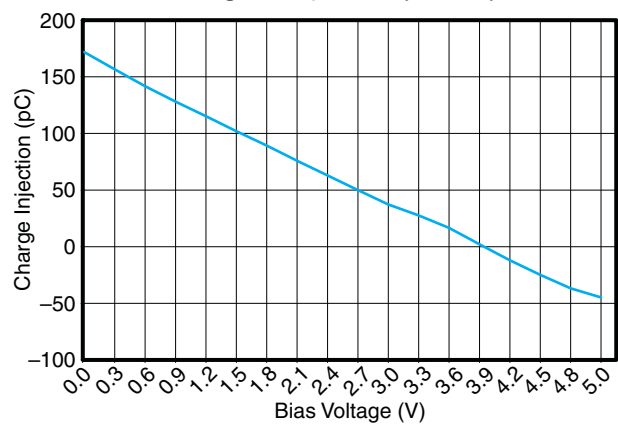


Figure 7. Charge Injection (Q_C) vs V_{COM} ($V_+ = 5$ V)

TYPICAL PERFORMANCE (continued)

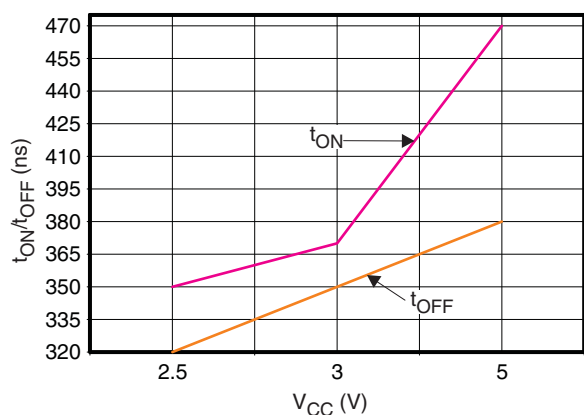
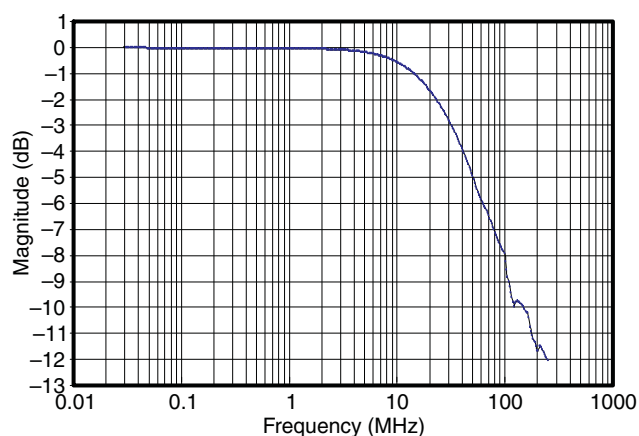
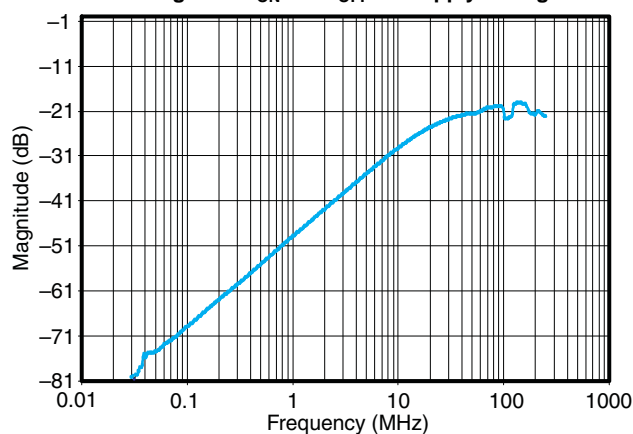
Figure 8. t_{ON} and t_{OFF} vs Supply VoltageFigure 9. Bandwidth (V₊ = 2.5 V)

Figure 10. OFF Isolation vs Frequency

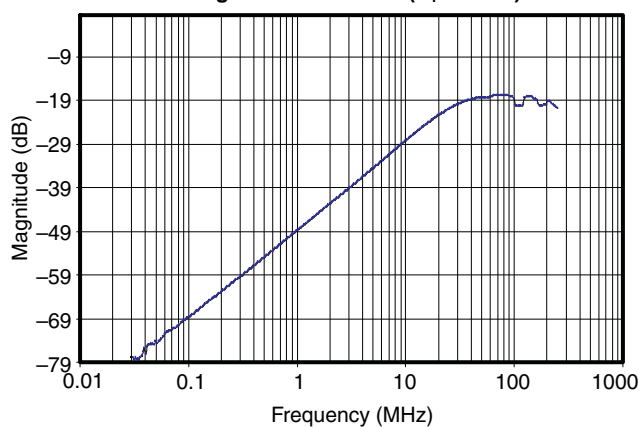
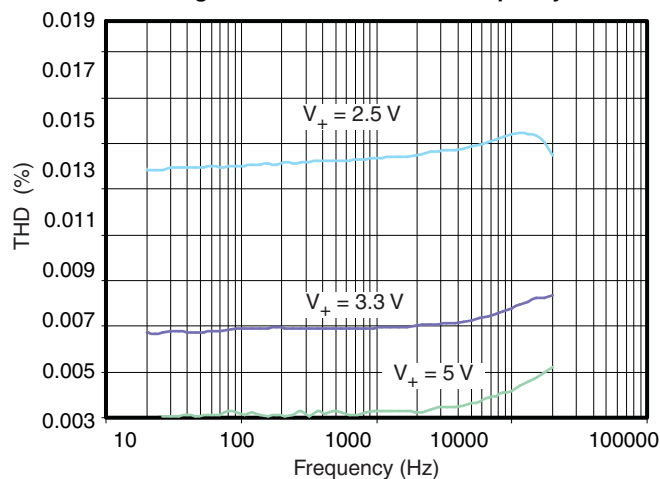
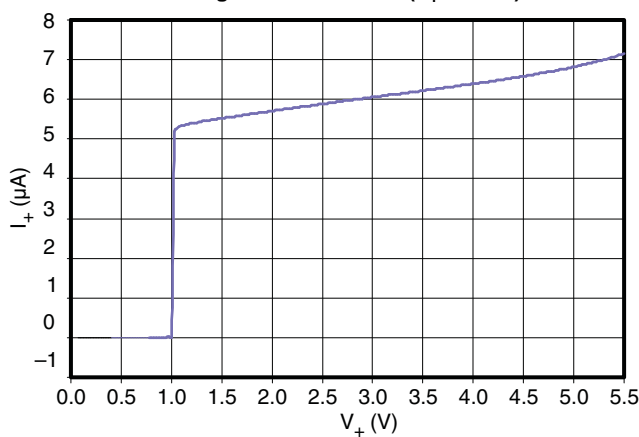
Figure 11. Crosstalk (V₊ = 3.3 V)

Figure 12. Total Harmonic Distortion vs Frequency

Figure 13. Power-Supply Current vs V₊

TYPICAL PERFORMANCE (continued)

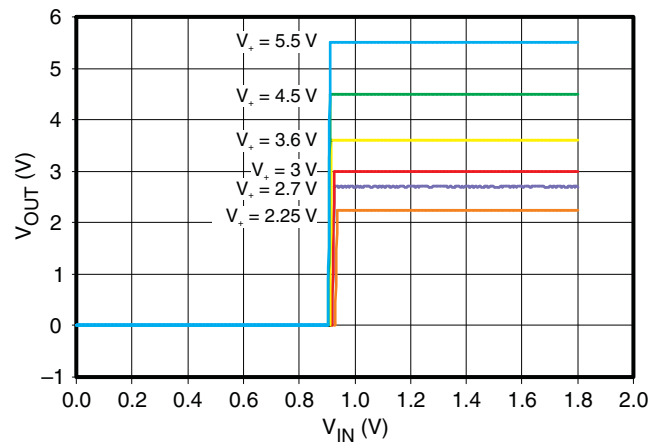


Figure 14. Control Input Thresholds

PARAMETER MEASUREMENT INFORMATION

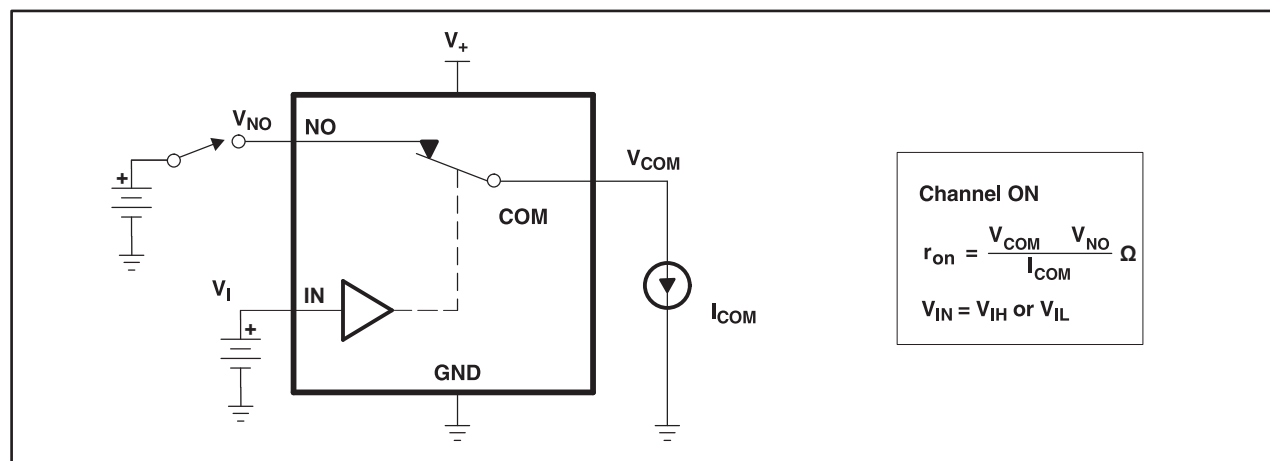


Figure 15. ON-state Resistance (r_{ON})

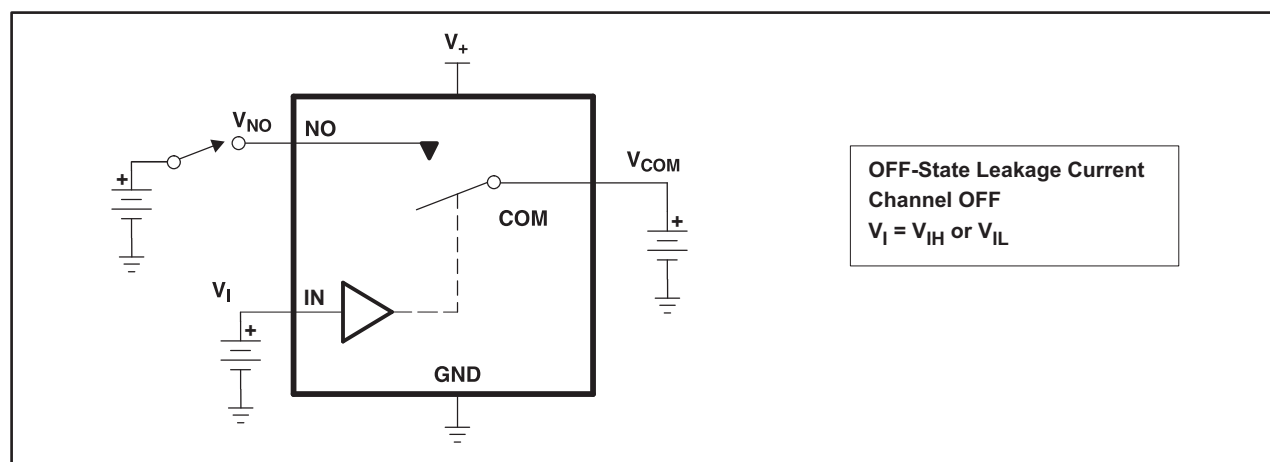


Figure 16. OFF-State Leakage Current
($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWROFF)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

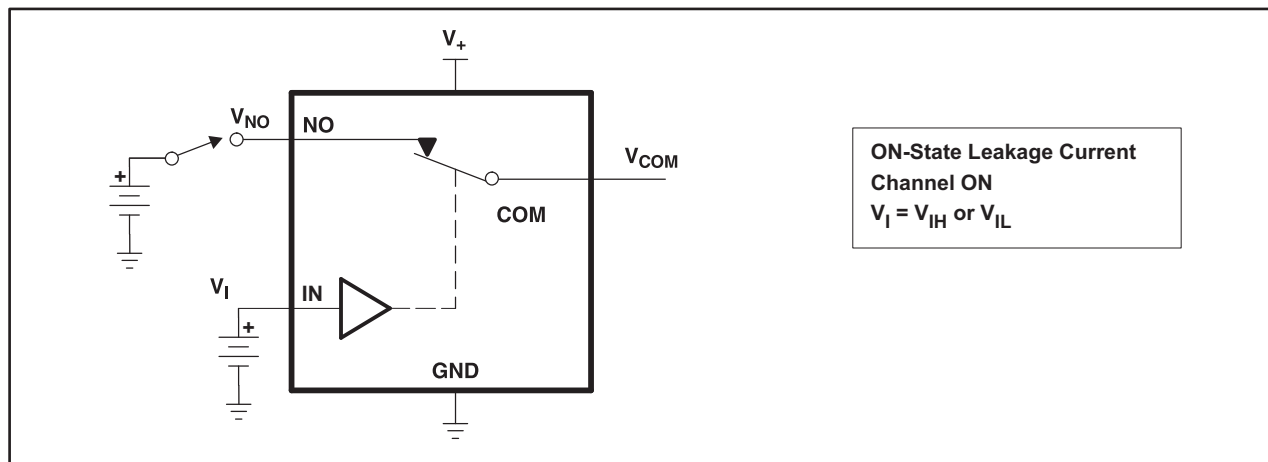


Figure 17. ON-State Leakage Current
($I_{COM(ON)}$, $I_{NC(ON)}$)

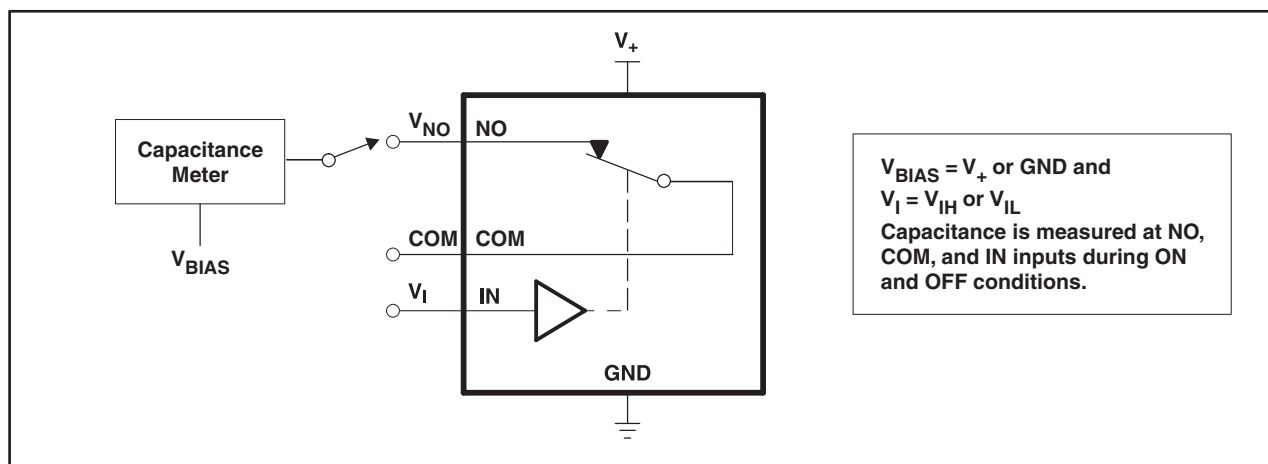
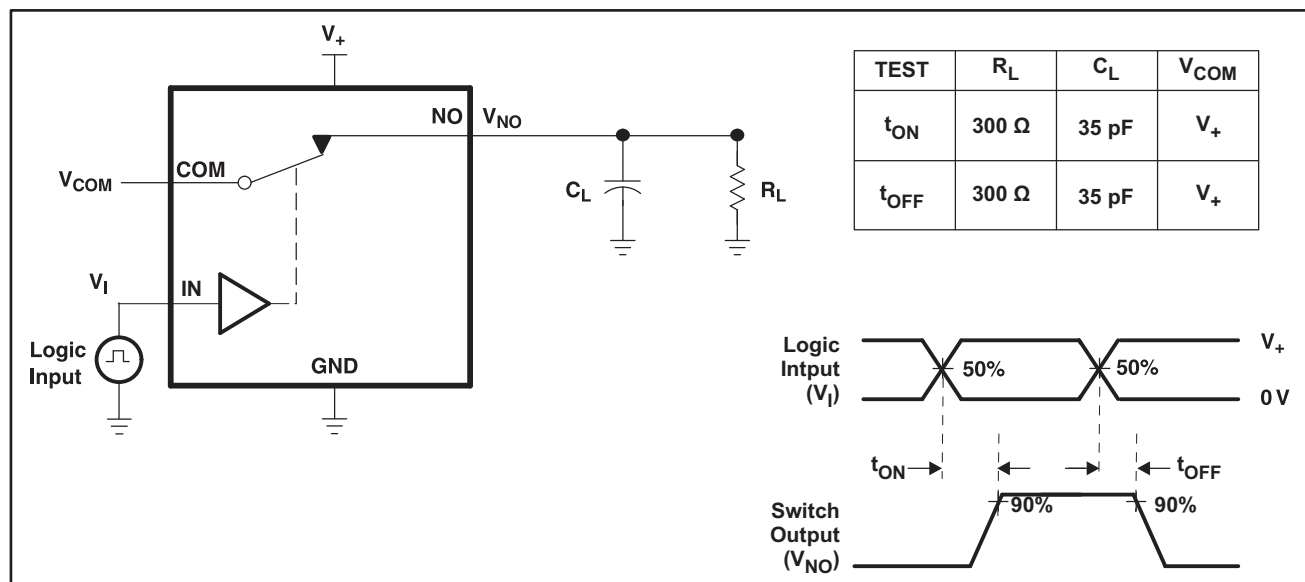


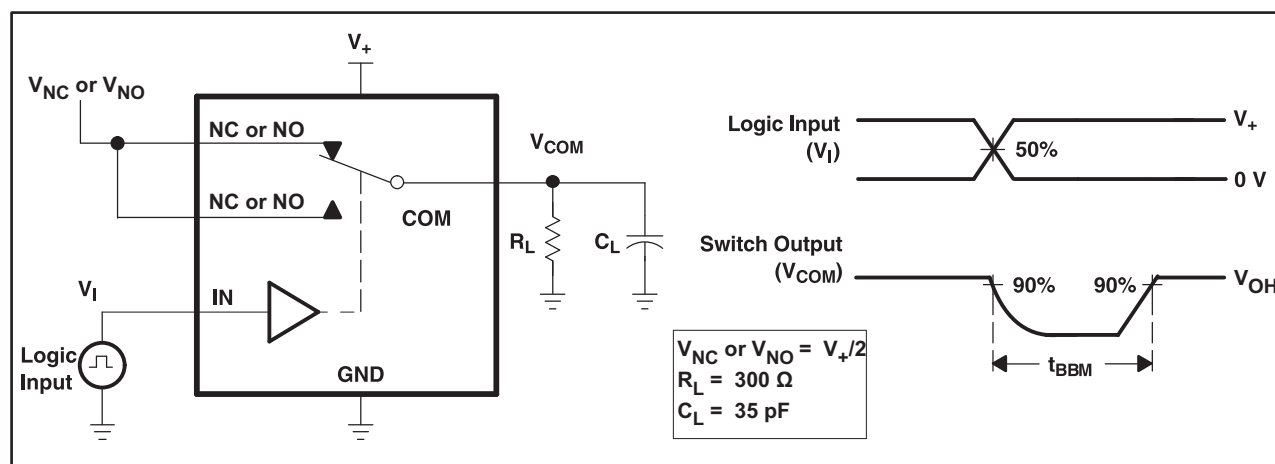
Figure 18. Capacitance
(C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

PARAMETER MEASUREMENT INFORMATION (continued)



- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50$ Ω , $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 19. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50$ Ω , $t_r < 5$ ns, $t_f < 5$ ns.

Figure 20. Break-Before-Make Time (t_{BBM})

PARAMETER MEASUREMENT INFORMATION (continued)

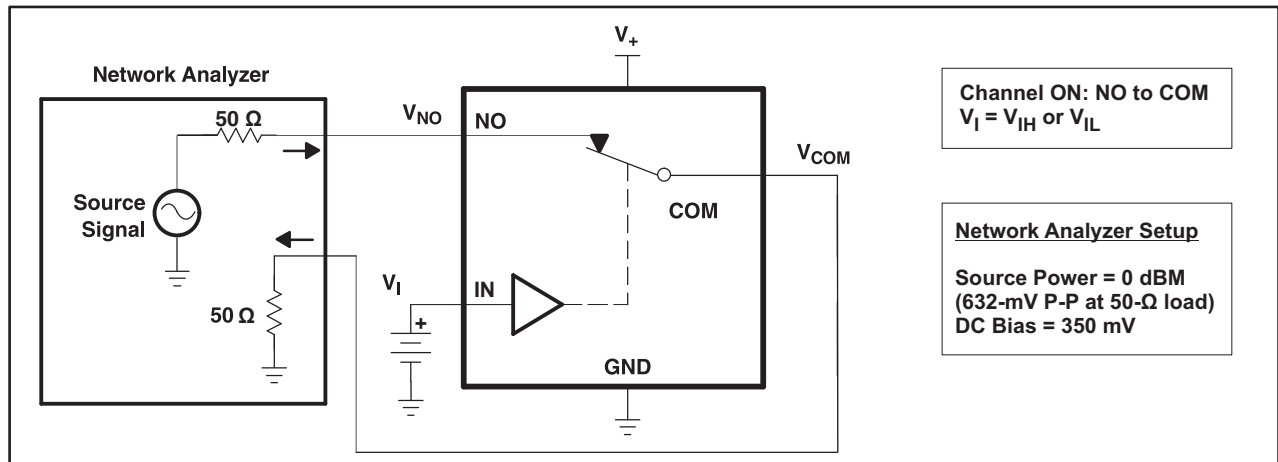


Figure 21. Bandwidth (BW)

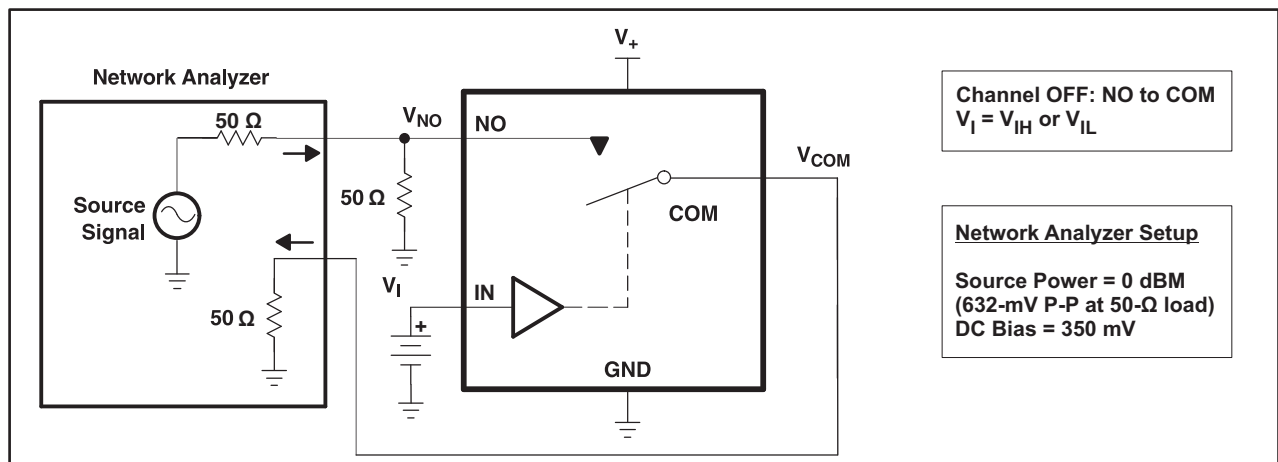


Figure 22. OFF Isolation (O_{iso})

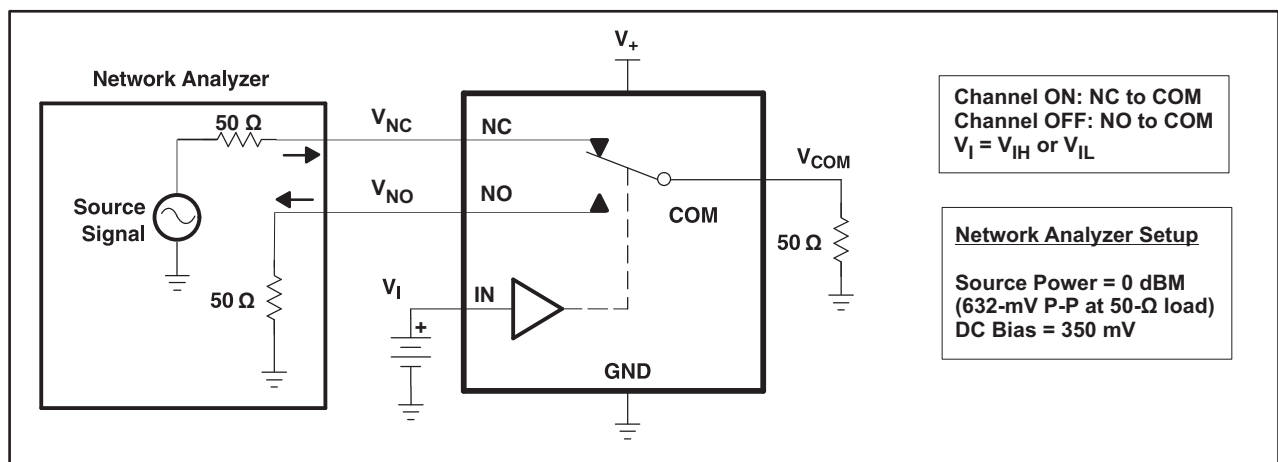
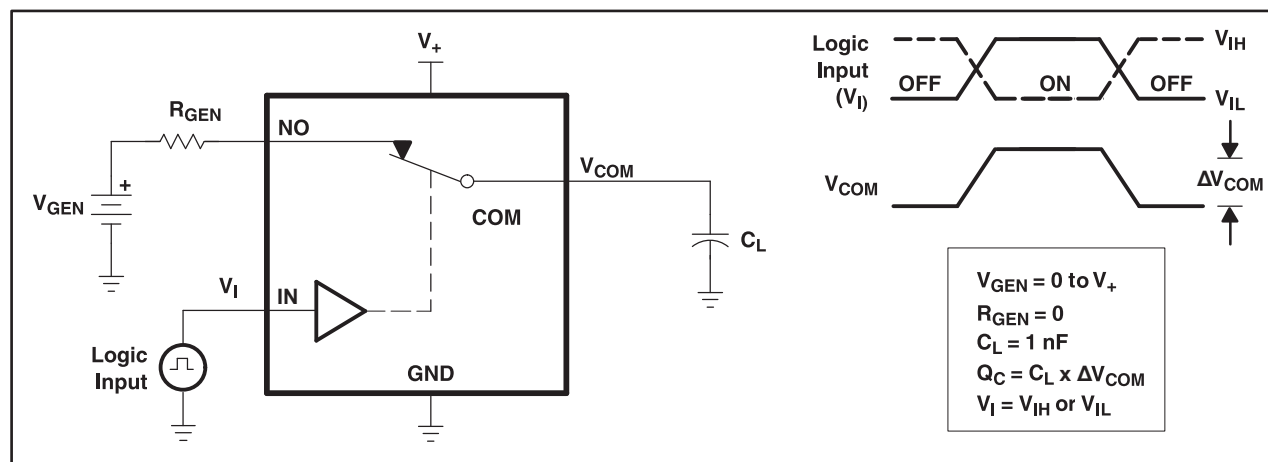
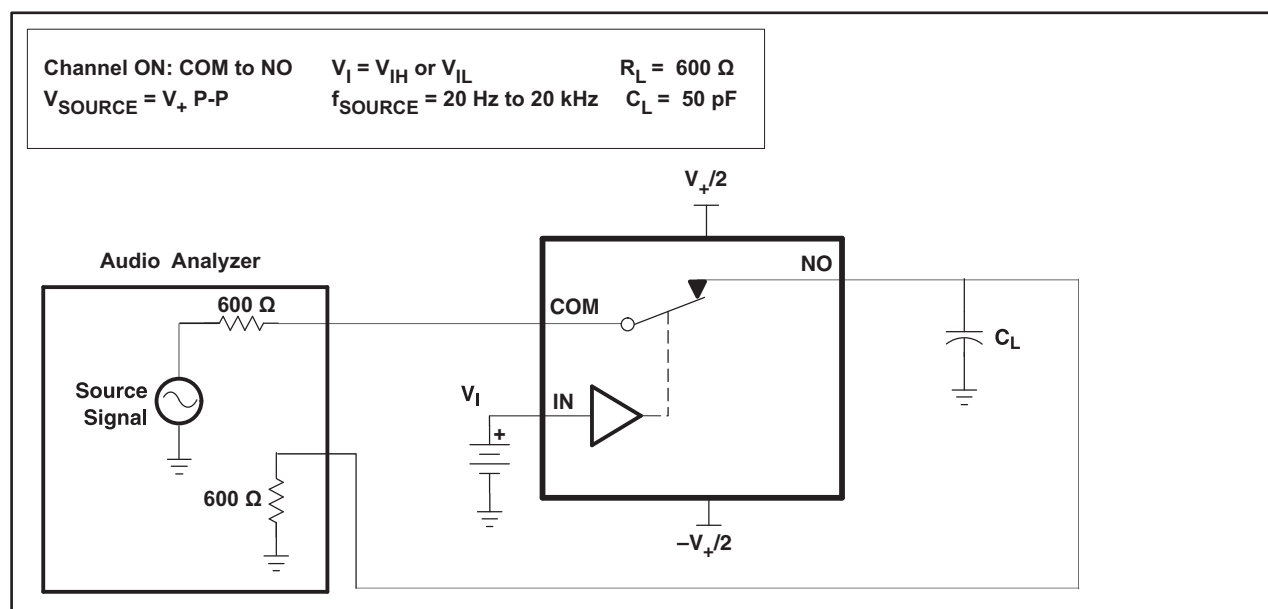


Figure 23. Crosstalk (X_{TALK})

PARAMETER MEASUREMENT INFORMATION (continued)



- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 24. Charge Injection (Q_C)

- A. C_L includes probe and jig capacitance.

Figure 25. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TS5A22366YFCR	ACTIVE	DSBGA	YFC	12	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

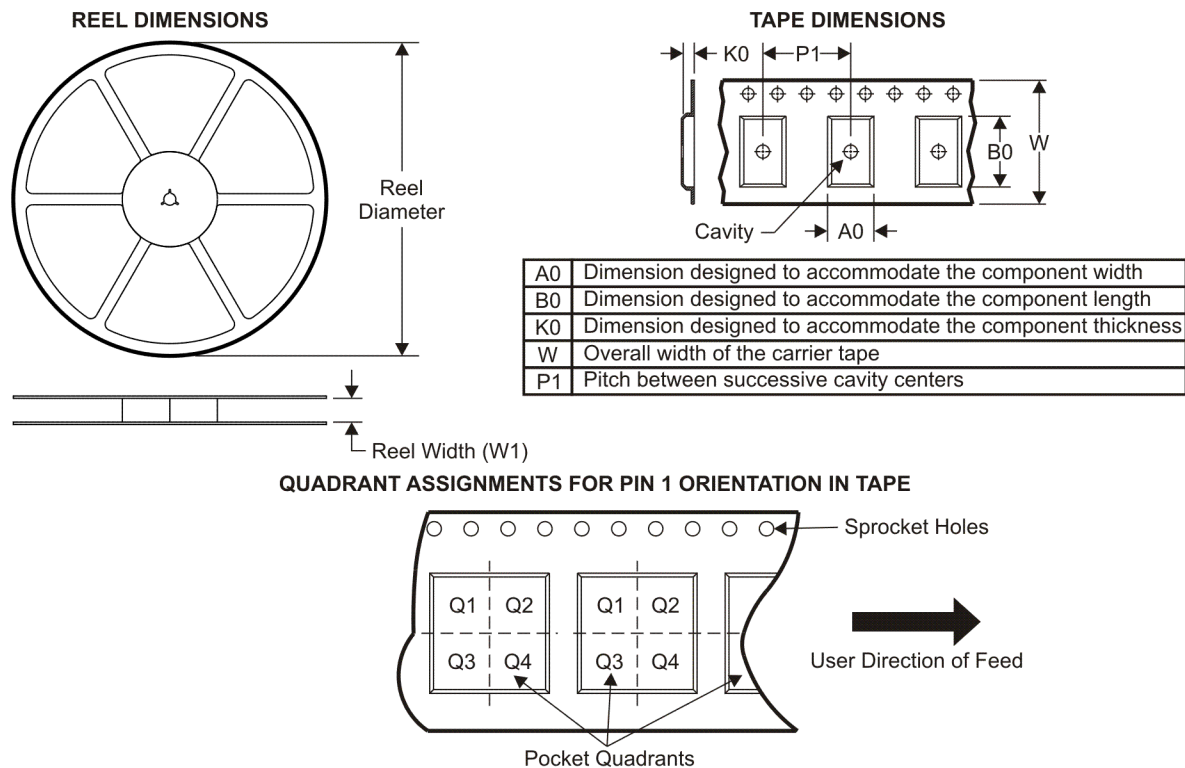
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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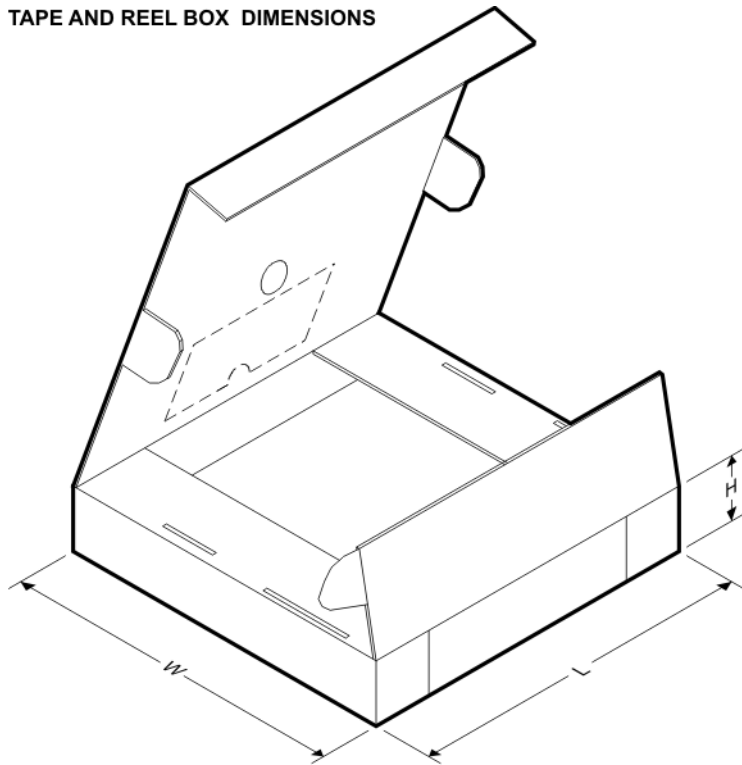
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22366YFCR	DSBGA	YFC	12	3000	180.0	8.4	1.29	1.69	0.73	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

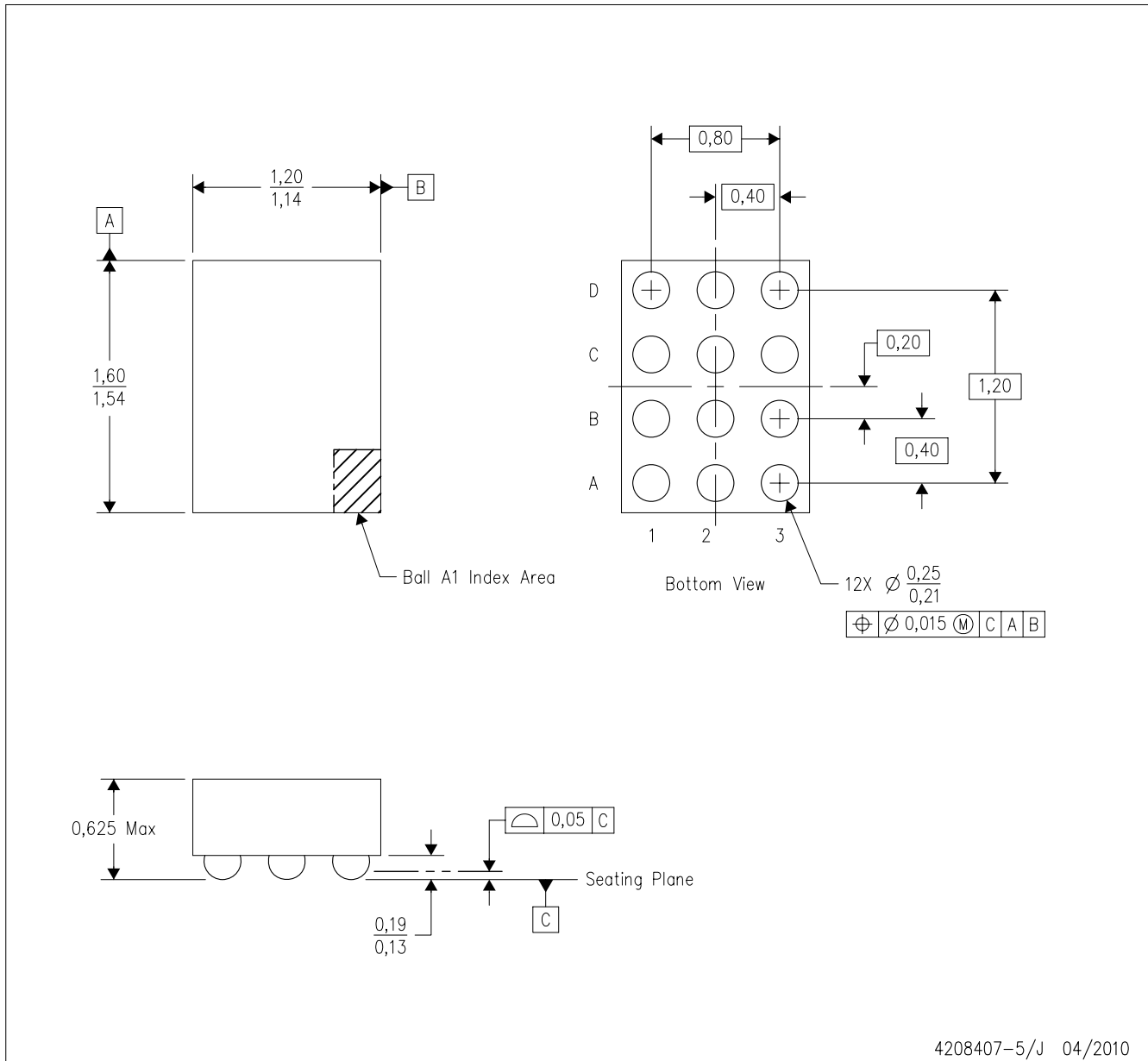


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22366YFCR	DSBGA	YFC	12	3000	220.0	220.0	34.0

YFC (R-XBGA-N12)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - NanoFree™ package configuration.
 - This is a Pb-free solder ball design.

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